MOS FET

Unit: mm

0. 16

FK8V03050L

## **Panasonic**

### FK8V03050L

#### Silicon N-channel MOSFET

For lithium-ion secondary battery protection circuit For DC-DC Converter

#### ■ Features

- Low drain-source On-state Resistance RDS(on) typ = 16 m $\Omega$  (VGS = 4.5 V)
- High-speed switching : Qg = 5.1 nC
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)
- Marking Symbol: 3E

#### ■ Packaging

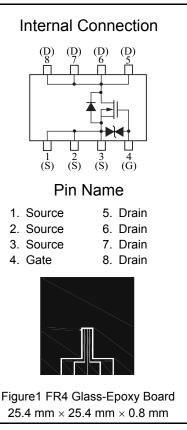
Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

4 8 (0.81)0.65 5. Drain 1. Source 2. Source 6. Drain 3. Source 7. Drain 8. Drain 4. Gate WMini8-F1 Panasonic JEITA SC-115 Code

| Parameter                                 | Symbol | Rating      | Unit |
|---|--------|-------------|------|
| Drain-source Voltage                      | VDS    | 33          | V    |
| Gate-source Voltage                       | VGS    | ±20         | V    |
| Drain Current (Steady State) *1           | ID     | 8           |      |
| Drain Current (t = 10 s) *1               | טו     | 10          |      |
| Drain Current (Pulsed) *1,*2              | IDp    | 32          | Α    |
| Source Current (Pulsed)                   | ISp    | 8           |      |
| (Body Diode) *1,*2                        | (BD)   | 0           |      |
| Total Power Dissipation (Steady State) *1 | PD     | 1           | W    |
| Total Power Dissipation (t = 10 s) *1     | וט     | 1.5         | VV   |
| Channel Temperature                       | Tch    | 150         | °C   |
| Operating Ambient Temperature             | Topr   | -40 to +85  | °C   |
| Storage Temperature Range                 | Tstg   | -55 to +150 | °C   |

Note) \*1 Device mounted on a glass-epoxy board (See Figure 1)

\*2 Pulse test: Ensure that the channel temperature does not exceed 150°C



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### ■ Electrical Characteristics Ta = 25°C ± 3°C

#### Static Characteristics

| Parameter                        | Symbol   | Conditions               | Min | Тур | Max | Unit |
|----------------------------------|----------|--------------------------|-----|-----|-----|------|
| Drain-source Breakdown Voltage   | VDSS     | ID = 1 mA, VGS = 0 V     | 33  |     |     | V    |
| Zero Gate Voltage Drain Current  | IDSS     | VDS = 33 V, VGS = 0 V    |     |     | 10  | μΑ   |
| Gate-source Leakage Current      | IGSS     | VGS = ±16 V, VDS = 0 V   |     |     | ±10 | μΑ   |
| Gate-source Threshold Voltage    | Vth      | ID = 0.73 mA, VDS = 10 V | 1   |     | 2.5 | V    |
| Drain-cource On-state Pecietance | RDS(on)1 | ID = 4A, VGS = 10 V      |     | 11  | 15  | mΩ   |
|                                  | RDS(on)2 | ID = 4A, VGS = 4.5 V     |     | 16  | 25  |      |

#### **Dynamic Characteristics**

| Input Capacitance            | Ciss    | VDS = 10 V, VGS = 0 V,        | 520 |     |
|------------------------------|---------|-------------------------------|-----|-----|
| Output Capacitance           | Coss    | f = 1 MHz                     | 110 | pF  |
| Reverse Transfer Capacitance | Crss    | 1 - 1 1011 12                 | 70  |     |
| Turn-on Delay Time *2        | td(on)  | VDD = 15 V, VGS = 0 to 10 V   | 8   |     |
| Rise Time *2                 | tr      | ID = 4 A                      | 4   | ns  |
| Turn-off Delay Time *2       | td(off) | VDD = 15 V, VGS = 10 to 0 V   | 32  | 115 |
| Fall Time *2                 | tf      | ID = 4 A                      | 10  |     |
| Total Gate Charge            | Qg      | VDD = 15 V, VGS = 0 to 4.5 V, | 5.1 |     |
| Gate-source Charge           | Qgs     | ID = 8 A                      | 1.8 | nC  |
| Gate-drain Charge            | Qgd     | ID - 0 A                      | 2.3 |     |

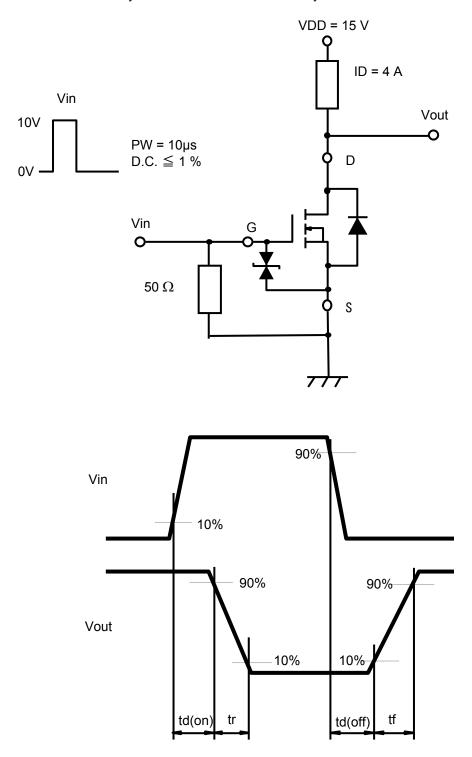
| Body Diode Characteristic |     |                     |     |     |   |
|---------------------------|-----|---------------------|-----|-----|---|
| Diode Forward Voltage *1  | VSD | IS = 4 A, VGS = 0 V | 0.8 | 1.2 | V |

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

<sup>2. \*1</sup> Pulse test: Ensure that the channel temperature does not exceed 150°C

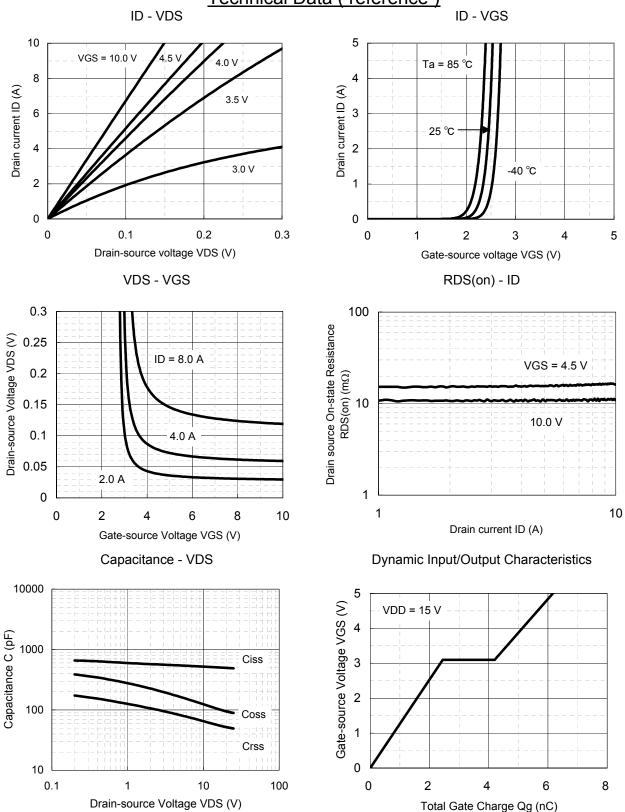
<sup>\*2</sup> Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

\*2 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time



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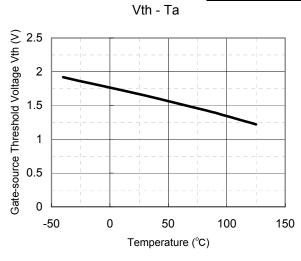
### Technical Data ( reference )

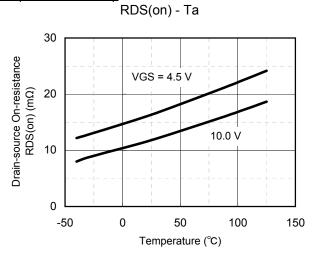


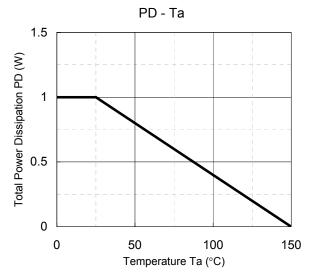
Page 4 of 6

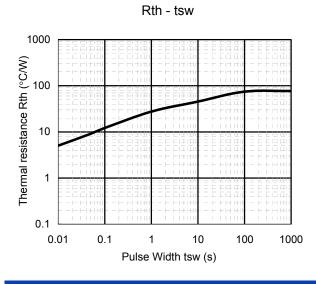
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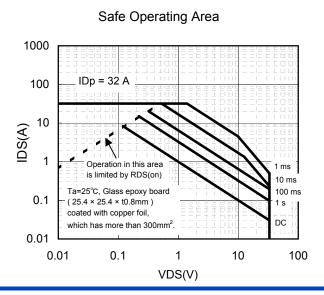
### Technical Data (reference)









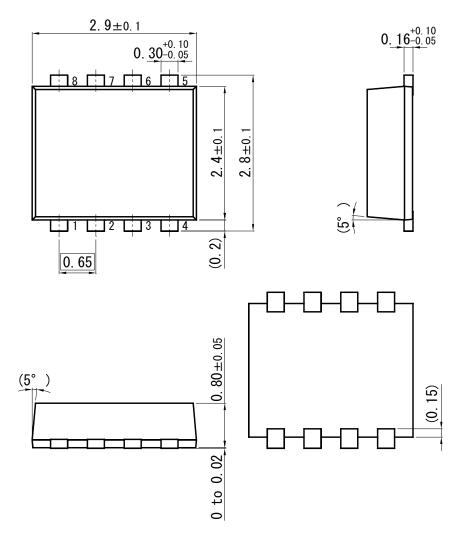


Page 5 of 6

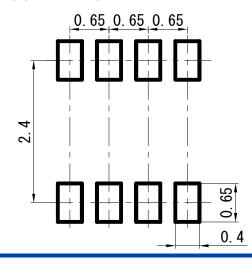
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WMini8-F1

Unit: mm



■ Land Pattern (Reference) (Unit: mm)



Page 6 of 6

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